

Claims

What is claimed is:

1. A method for forming a highly conductive, substantially transparent film on a substrate,

5 comprising:

providing a substrate;

depositing on the substrate, at a temperature of 120 °C or less, a layer of amorphous and/or polycrystalline conductive material which is substantially optically transparent to visible wavelengths in its crystalline state; and

directing pulsed energy onto the layer of conductive material to crystallize it and form the highly conductive, substantially optically transparent film.

2. The method of claim 1, wherein the step of providing a substrate further comprises providing a substrate composed of a material selected from the group consisting of PET, PEN, PC, PAR, PEL, PES, PI, Teflon PFA, PEEK, PEK, PETFE and PMMA.

3. The method of claim 1, wherein the step of providing a substrate further comprises providing a substrate coated with an optically transparent thermal insulating layer.

20 4. The method of claim 3, wherein the thermal insulating layer further comprises an oxide, a nitride and/or a polymer.

5. The method of claim 1, wherein the layer of conductive, transparent material is selected from the group containing Indium Tin Oxide, Zinc Stannate, Cadmium Stannate, Zinc Indium Oxide, Magnesium Indium Oxide and Gallium Indium Oxide.

6. The method of claim 1, wherein the step of depositing the conductive material on a surface of the substrate further comprises depositing the conductive material by sputtering, reactive sputtering, evaporation, reactive evaporation, chemical vapor deposition or plasma enhanced chemical vapor deposition.

7. The method of claim 1, wherein the step of directing pulsed energy onto the layer of conductive material further comprises the steps of:

generating an energy pulse from a laser, an electron beam source or an ion beam source; and

directing the energy pulse onto the layer of conductive material.

8. The method of claim 7, wherein the step of generating an energy pulse further comprises generating an energy pulse from an excimer laser or a YAG laser.

9. The method of claim 7 wherein the step of directing an energy pulse further comprises directing an energy pulse having a wavelength of between 200 and 400 nm onto the layer of conductive material.

10. The method of claim 9, wherein the step of generating an energy pulse further comprises generating an energy pulse from an excimer laser.

11. The method of claim 9, wherein the step of generating an energy pulse further comprises
5 generating an energy pulse from a YAG laser.

12. A composite material for use in fabricating semiconductor display devices, comprising:
a substrate that is intolerant of temperatures greater than 350°C; and
a layer of crystalline material that is highly conductive and substantially optically
transparent to visible wavelengths on one surface of the substrate.

13. The composite material of claim 12, wherein the substrate is a material selected from the
group consisting of PET, PEN, PC, PAR, PEL, PES, PI, Teflon PFA, PEEK, PEK, PETFE and
PMMA.

14. The composite material of claim 12, wherein the layer of conductive, transparent material is
selected from the group containing Zinc Oxide, Indium Tin Oxide, Zinc Stannate, Cadmium
Stannate, Zinc Indium Oxide, Magnesium Indium Oxide and Gallium Indium Oxide.

15. A composite material for use in fabricating semiconductor display devices, comprising:
a substrate that is intolerant of temperatures greater than 350°C;
a layer of thermal insulating material that is substantially optically transparent at
visible wavelengths on one surface of the substrate; and

